

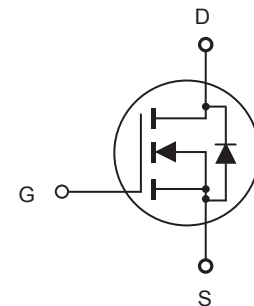
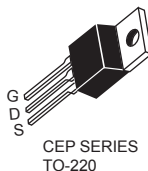


CEP703AL/CEB703AL

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 30V, 40A, $R_{DS(ON)} = 17m\Omega$ @ $V_{GS} = 10V$.
 $R_{DS(ON)} = 30m\Omega$ @ $V_{GS} = 4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	40	A
Drain Current-Pulsed ^a	I_{DM}	120	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P_D	50	W
		0.4	W/ $^\circ\text{C}$
Operating and Store Temperature Range	T_J, T_{stg}	-65 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

[查询"CEP703AL_06"供应商](#)

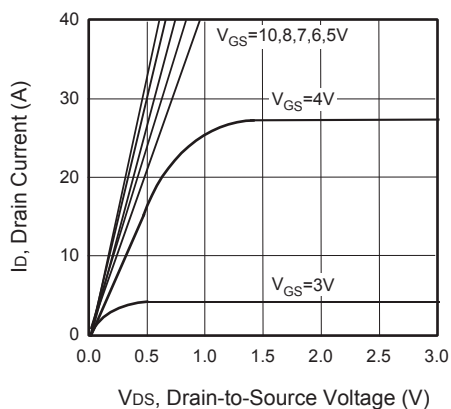


Figure 1. Output Characteristics

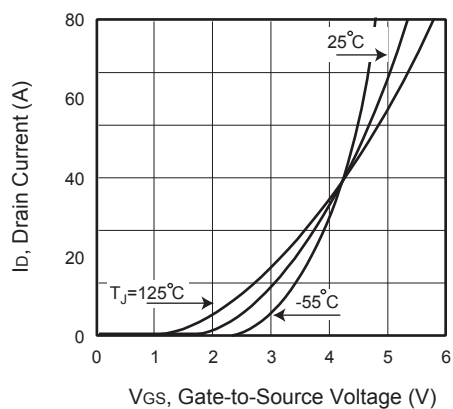


Figure 2. Transfer Characteristics

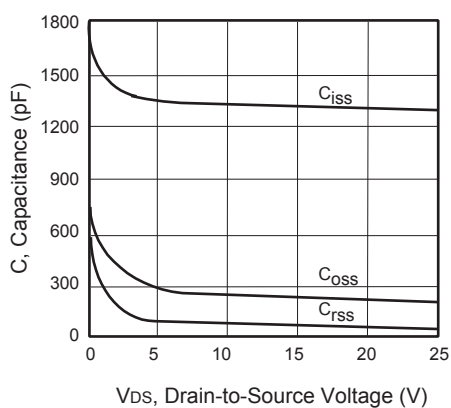


Figure 3. Capacitance

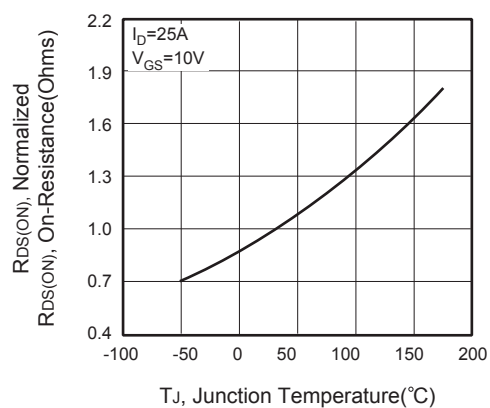


Figure 4. On-Resistance Variation with Temperature

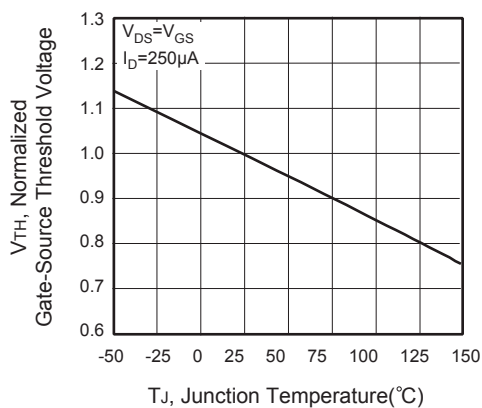


Figure 5. Gate Threshold Variation with Temperature

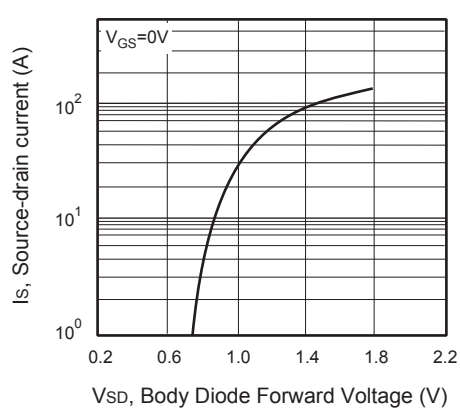


Figure 6. Body Diode Forward Voltage Variation with Source Current

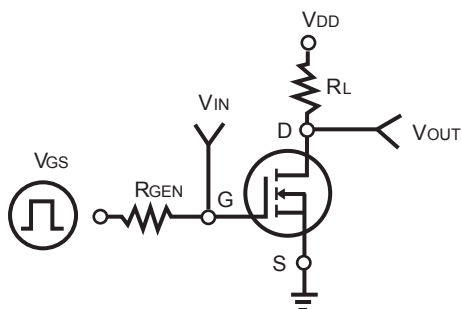
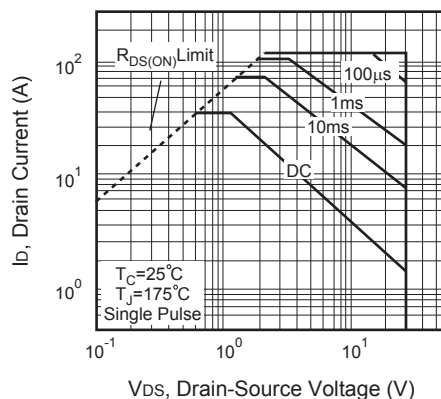
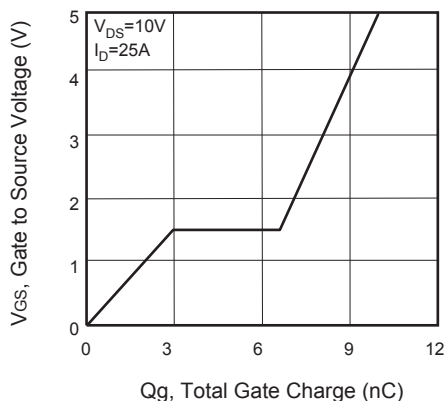


Figure 9. Switching Test Circuit

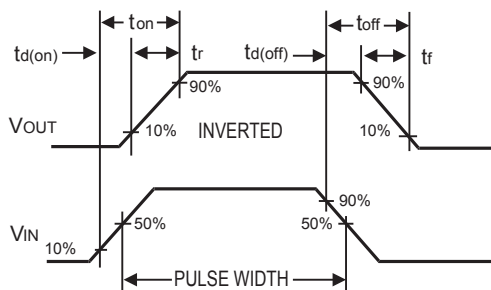


Figure 10. Switching Waveforms

